

Please amend the application as follows.

IN THE SPECIFICATION:

Please replace the paragraph at page 1, lines 5 - 11, with the following rewritten paragraph:

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-- This application is a continuation application of Application Serial No. 09/421,467, filed October 19, 1999, which is ^{abandoned} ~~currently pending~~. Application Serial No. 09/421,467 is a continuation-in-part of the following applications: Serial No. 09/251,588, filed February 17, 1999, which is abandoned; Serial No. 09/251,826, filed February 17, 1999, which issued as U.S. Patent No. 6,323,132, on November 27, 2001; and Serial No. 09/251,633, which issued as U.S. Patent No. 6,265,318, on July 24, 2001. Application Serial Nos. 09/251,588; 09/251,826; and 09/251,633 are continuations-in-part of Application Serial No. 09/006,092, filed January 13, 1998, which is abandoned. -- *ns 2/24/03*

Please delete the paragraph at page 1, lines 12 - 24, in its entirety.

IN THE ABSTRACT:

Please replace the Abstract, at page 118, lines 4 - 18, with the following rewritten Abstract:

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-- A method of etching a noble metal electrode layer disposed on a substrate to produce a semiconductor device including a plurality of electrodes separated by a distance equal to or less than about 0.35 μm and having a noble metal profile equal to or greater than about 80°. The method comprises heating the substrate to a temperature greater than about 150°C, and etching the noble metal electrode layer by employing a high density inductively coupled plasma of an etchant gas comprising a gas selected from the group consisting of nitrogen, oxygen, a halogen (e.g., chlorine), argon, and a gas selected from the group consisting of BCl_3 , HBr , and SiCl_4 mixtures thereof.